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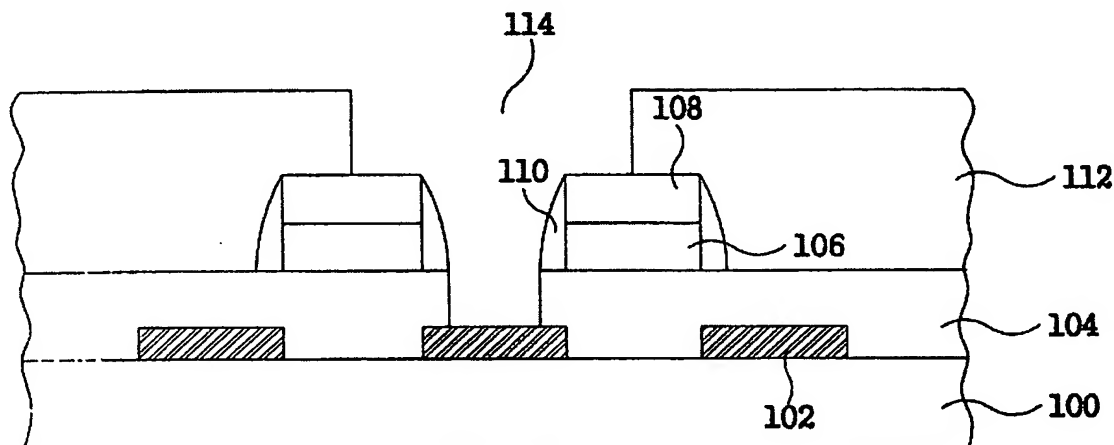
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(54) Title: **METHOD FOR DEPOSITING NITRIDE FILM USING CHEMICAL VAPOR DEPOSITION APPARATUS OF SIN-  
 GLE CHAMBER TYPE**



(57) **Abstract:** The present invention relates to a method for depositing a nitride film using a chemical vapor deposition apparatus of single chamber type, and more particularly to a method for depositing a nitride film that is capable of depositing the nitride film in which an area of the nitride film at the top of an interlayer isolation film has a larger thickness compared to each area thereof at the sides and the bottom of the interlayer isolation film and/or a contact hole by regulating a mixture ratio of an ammonia gas and a silane gas, both of which being process gases, using a chemical vapor deposition apparatus of single chamber type.